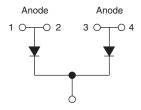


Not Insulated SOT-227 Power Module U-Series FRED Pt® Gen 4, 600 V



SOT-227



Base common cathode

PRIMARY CHARACTERISTICS						
V_{R}	600 V					
$I_{F(AV)}$ at T_C = 124 °C per module ⁽¹⁾	450 A					
t _{rr}	97 ns					
Туре	Modules - Diode FRED Pt®					
Package	SOT-227					
Circuit configuration	Common cathode					

Note

(1) All 4 anode terminals connected

FEATURES

- Gen 4 FRED Pt® dices technology
- Ultrasoft reverse recovery characteristics
- Low I_{RRM} and reverse recovery charge
- · Very low forward voltage drop
- · Not insulated package
- 175 °C operating junction temperature
- Optimized for power conversion: welding and industrial SMPS applications
- Plug-in compatible with other SOT-227 packages
- Easy to assemble
- · Direct mounting to heatsink
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION

Gen 4 FRED technology, state of the art, ultra low V_F , soft switching optimized for IGBT F/W diode.

The minimized conduction loss, optimized storage charge and low recovery current minimized the switching losses and reduce the over dissipation in the switching element and snubbers.

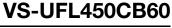
ABSOLUTE MAXIMUM RATINGS (T _J = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V_{R}		600	V	
Continuous forward current per diode	I _F	T _C = 133 °C	250	۸	
Single pulse forward current per diode	I _{FSM}	T_C = 25 °C, 10 ms sine or 6 ms rectangular pulse	1170	Α	
Maximum power dissipation per module	P_D	T _C = 135 °C	727	W	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	



ELECTRICAL SPECIFICATIONS PER DIODE (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V_{BR}	I _R = 500 μA	600	-	-		
Forward voltage, per leg		I _F = 100 A	-	1.18	1.32	V	
	V _{FM}	I _F = 100 A, T _J = 125 °C	-	1.00	-		
		I _F = 100 A, T _J = 175 °C	-	0.91	-		
		I _F = 200 A	-	1.34	1.60		
		I _F = 200 A, T _J = 125 °C	-	1.19	-		
		I _F = 200 A, T _J = 175 °C	-	1.11	-		
Reverse leakage current, per leg I _{RM}	I _{RM}	$V_R = V_R = 600 \text{ V},$	-	0.2	150	μΑ	
		V _R = V _R = 600 V, T _J = 125 °C	-	169	-		
		V _R = V _R = 600 V, T _J = 175 °C	-	2.1	-	mA	
Junction capacitance, per leg	Ст	V _B = 600 V, f = 1 MHz	-	173	-	pF	

DYNAMIC RECOVERY CHARACTERISTICS PER DIODE (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Devenue receivementime nerview	Para de la companya della companya della companya della companya de la companya della companya d	T _J = 25 °C	I _F = 50 A dI _F /dt = 500 A/μs V _R = 200 V	-	97	-	ns
Reverse recovery time, per leg t _{rr}	L _{FF}	T _J = 125 °C		-	164	-	
Peak recovery current, per leg I _{RRM}	_	T _J = 25 °C		-	16	-	Α
	IRRM	T _J = 125 °C		-	33	-	
Reverse recovery charge, per leg	Q _{rr}	T _J = 25 °C		-	794	-	nC
		T _J = 125 °C		-	2736	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	В		-	-	0.11	
Junction to case, both leg conducting	R_{thJC}		-	-	0.055	°C/W
Case to heatsink, per module	R _{thCS}	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting targue		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
Mounting torque		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style				SOT	-227	





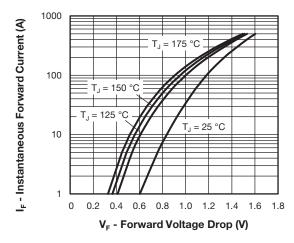


Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

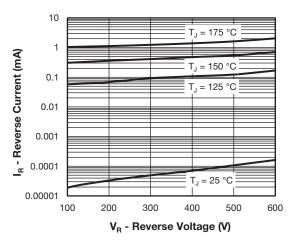


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

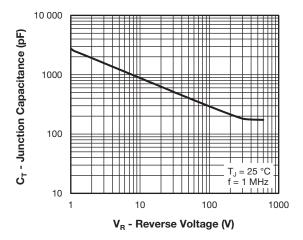


Fig. 3 - Typical Junction Capacitance vs Reverse Voltage (Per Diode)

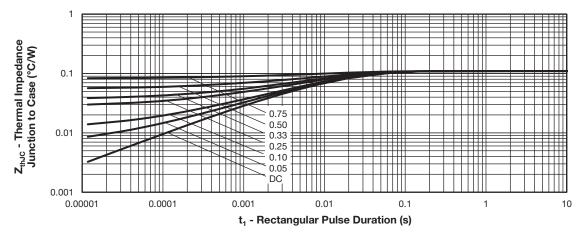
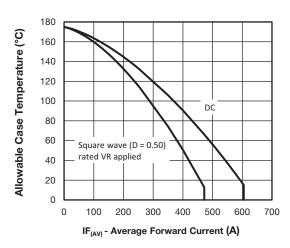


Fig. 4 - Maximum Thermal Impedance Junction-to-Case Characteristics (Per Diode)



www.vishay.com

Fig. 5 - Maximum Current Rating Capability (Per Diode)

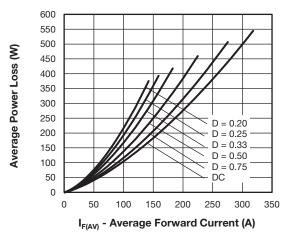


Fig. 6 - Forward Power Loss Characteristics (Per Diode)

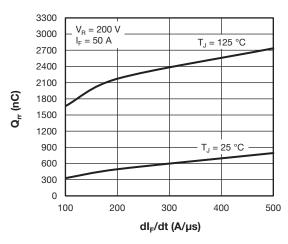


Fig. 7 - Typical Reverse Recovery Charge vs. dI_F/dt (Per Diode)

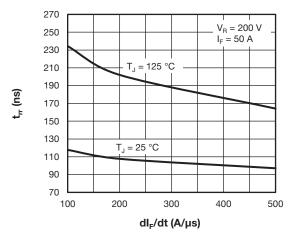


Fig. 8 - Typical Reverse Recovery Time vs. dl_F/dt (Per Diode)

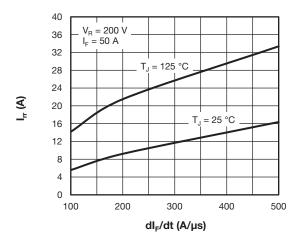
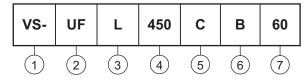


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt (Per Diode)

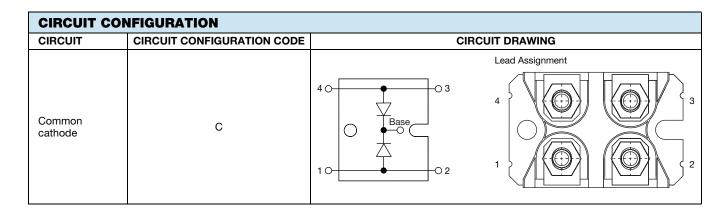
ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Ultrafast rectifier
- Ultrafast Pt diffused, low V_F
- Current rating (450 = 450 A)
- 5 Circuit configuration (2 common cathode diodes)
- Package indicator (SOT-227 standard not insulated)
- 7 Voltage rating (60 = 600 V)

Quantity per tube is 10 pcs, M4 screw and washer included

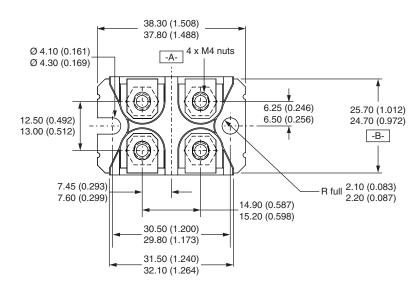


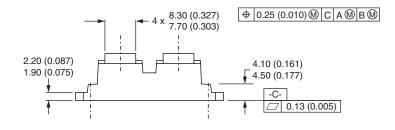
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?95423</u>						
Part marking information	www.vishay.com/doc?95425					

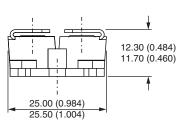


SOT-227 Generation II

DIMENSIONS in millimeters (inches)







Note

• Controlling dimension: millimeter



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.